

# **TSM3404**

#### 30V N-Channel MOSFET



**SOT-23** 

#### Pin Definition:

3 1. Gate 2. Source

3. Drain

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
30	28 @ V <sub>GS</sub> = 10V	5.8
	43 @ V <sub>GS</sub> = 4.5V	5.0

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

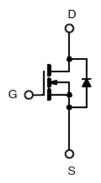
#### **Application**

- Load Switch
- PA Switch

#### **Ordering Information**

Part No.	Package	Packing
TSM3404CX RF	SOT-23	T&R

#### **Block Diagram**



N-Channel MOSFET

### Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	30V	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current, V <sub>GS</sub> @10V.		I <sub>D</sub>	5.8	А	
Pulsed Drain Current, V <sub>GS</sub> @10V		I <sub>DM</sub>	20	А	
Continuous Source Current (Diode Co	nduction) <sup>a,b</sup>	I <sub>S</sub>	2.5	А	
Mariana Parana Diania atian	Ta = 25 °C		1.4	W	
Maximum Power Dissipation	Ta = 75 °C	$P_D$	1		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temp	erature Range	T <sub>J</sub> , T <sub>STG</sub> -55 to +150		°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖ <sub>JF</sub>	43	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ <sub>JA</sub>	65	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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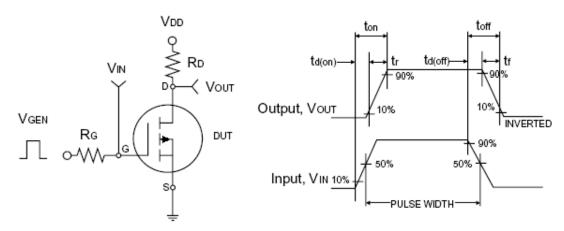


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30		-	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.4	3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>	-		±1.5	μA
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	μA
On-State Drain Current	$V_{DS} = 5V$ , $V_{GS} = 4.5V$	I <sub>D(ON)</sub>	20		-	Α
Proin Course On State Besistance	$V_{GS} = 10V, I_D = 5.8A$		1	22	28	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 5A$	R <sub>DS(ON)</sub>		35	44	
Forward Transconductance	$V_{DS} = 5V$ , $I_D = 5.0A$	g <sub>fs</sub>		25		S
Diode Forward Voltage	I <sub>S</sub> = 1.0A, V <sub>GS</sub> = 0V	$V_{SD}$		0.76	1	V
Dynamic <sup>b</sup>	_					
Total Gate Charge	\/ - 15\/   - 5 9A	$Q_g$		4.52		
Gate-Source Charge	$V_{DS} = 15V, I_D = 5.8A,$ $V_{GS} = 10V$	$Q_gs$	-	1.24	-	nC
Gate-Drain Charge	V <sub>GS</sub> = 10V	$Q_{gd}$		1.68		
Input Capacitance	\/ - 45\/ \/ - 0\/	$C_{iss}$	-	400.96	-	
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	$C_{oss}$	-	100.47	-	pF
Reverse Transfer Capacitance	1 - 1.0101112	$C_{rss}$	-	71.82	-	
Switching <sup>c</sup>						
Turn-On Delay Time		t <sub>d(on)</sub>		7.42	-	
Turn-On Rise Time	$V_{DD} = 15V, R_L = 2.2\Omega,$	t <sub>r</sub>		3.41	-	nS
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$ $R_G = 6\Omega$	t <sub>d(off)</sub>	-	20.4	-	113
Turn-Off Fall Time	NG - 077	t <sub>f</sub>		3.01		

#### Notes:

- a. pulse test: PW  $\leq 300 \mu S$ , duty cycle  $\leq 2\%$  b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

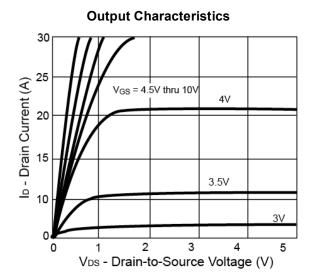




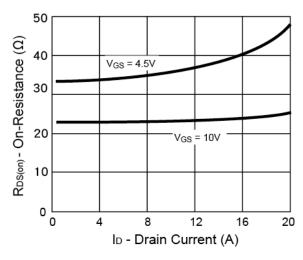




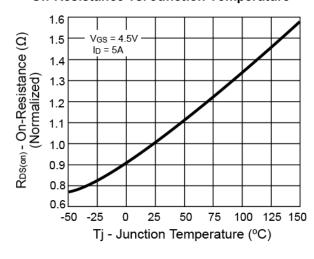
#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)



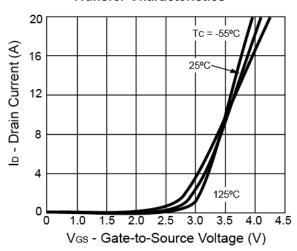
#### On-Resistance vs. Drain Current



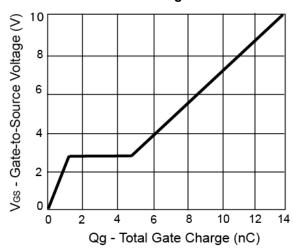
#### On-Resistance vs. Junction Temperature



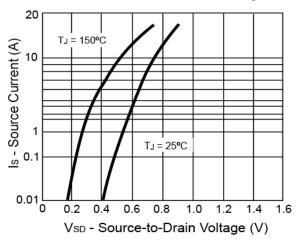
#### **Transfer Characteristics**



#### **Gate Charge**



#### Source-Drain Diode Forward Voltage





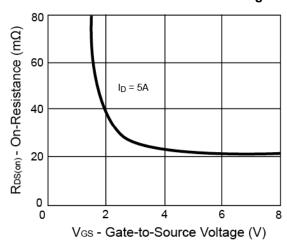


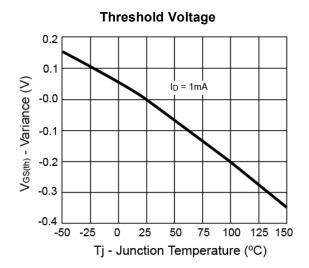




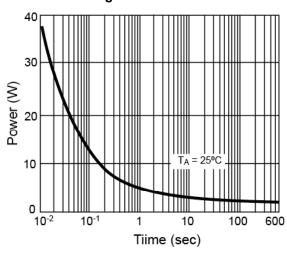
#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

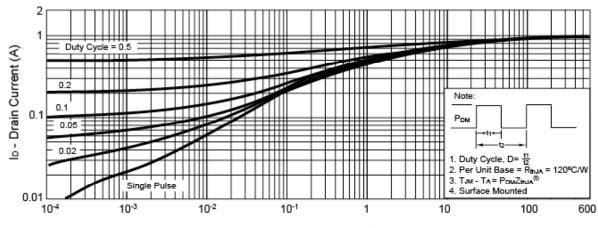




**Single Pulse Power** 



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

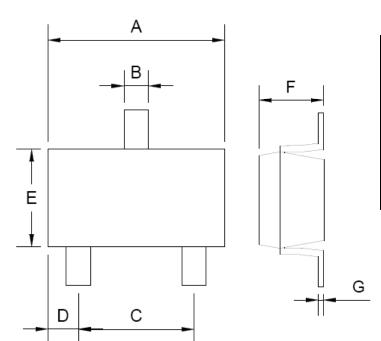


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# **SOT-23 Mechanical Drawing**



SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	2.88	2.91	0.113	0.115	
В	0.39	0.42	0.015	0.017	
С	1.78	2.03	0.070	0.080	
D	0.51	0.61	0.020	0.024	
Е	1.59	1.66	0.063	0.065	
F	1.04	1.08	0.041	0.043	
G	0.07	0.09	0.003	0.004	



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